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High resolution mapping of non-patterned MRAM film stacks

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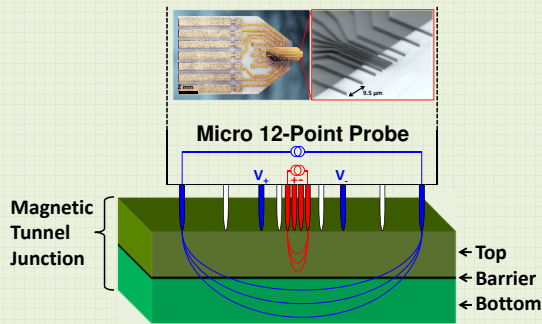


Production challenge¹⁻³

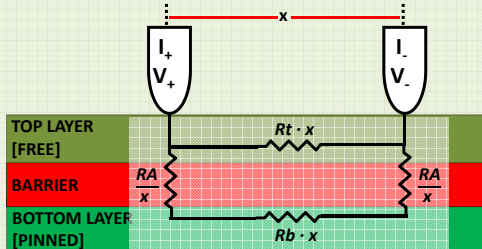
- Unacceptable RA variations across the wafer
- Optimization of production tools requires information of variations

Standard CIPT measurement routine⁴

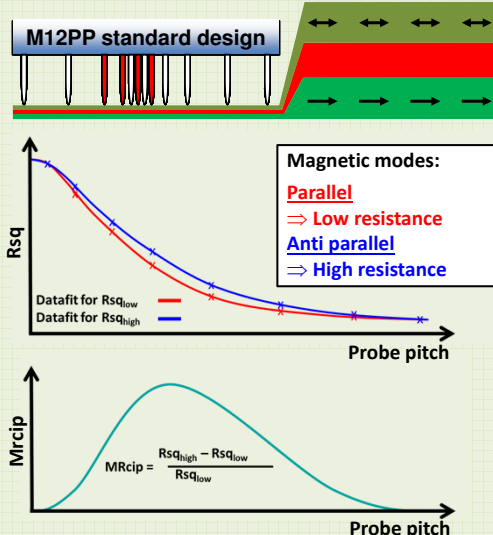
- Switching magnetic field
- Rt, Rb, TMR and RA is measured
- ~94 s / point
- Measurement time is the limiting factor for high density mapping



Two-point measurements on MTJ



Four-point measurements on MTJ



RA is the deciding parameter⁵⁻⁸

- TMR is maintained at a steady level till close proximity of the edge of the processed area
- Variations in TMR are radially symmetric
- RA starts to decrease significantly at a distance of 50 mm from the wafer center
- Variations in RA are radially asymmetric
- Full wafer map is needed for process optimization

Sample: 200 mm non-patterned MTJ, Co₄₀Fe₄₀B₂₀/1 nm MgO/Co₄₀Fe₄₀B₂₀

Figure 1

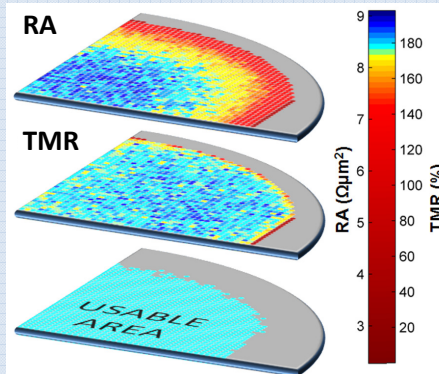


Fig. 1. Mapping of RA and TMR with 2 mm step size (1613 points) on a quarter of the sample. Usable wafer area is based on a +/-10 % limit with respect to the mean value at the center of the wafer.

Figure 2

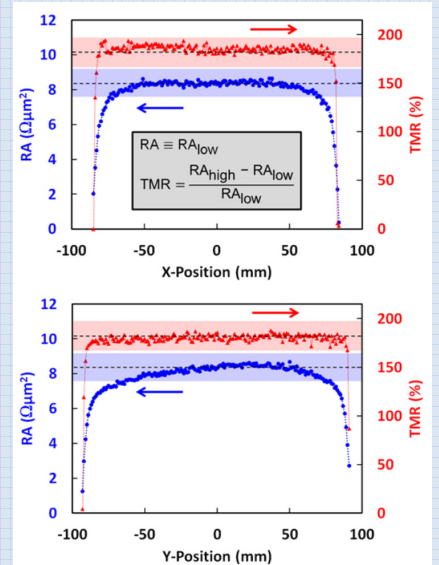


Fig. 2. Line scan measurements of RA and TMR with a step size of 1 mm along the X-axis (upper graph) and Y-axis (lower graph) across the sample. The colored areas behind the plots mark a +/-10 % band with respect to the mean values indicated by the dashed lines.

New static field CIPT measurement routine

- Static magnetic field
- Rt, Rb and RA is measured
- ~13 s / point

Measurement time is reduced by a factor of 7

Figure 3

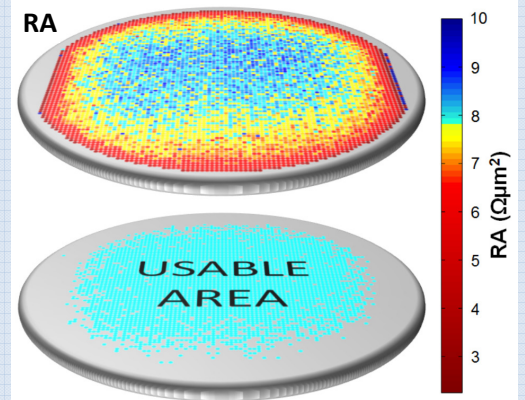


Fig. 3. High density map of RA on the full 200 mm wafer obtained with 2 mm step size totaling 6571 measurement points. The usable wafer area vs. edge exclusion zone is based on an acceptance limit of +/-10 % with respect to the mean value at the center of the wafer.

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